

NTHL075N065SC1

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	1.01	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	650	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 20\text{ mA}$, referenced to 25°C				

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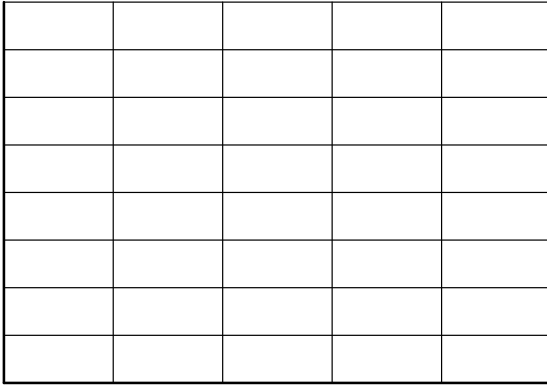
ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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DRAIN-SOURCE DIODE CHARACTERISTICS

Reverse Recovery Time	t_{RR}	$V_{GS} = -5/18\text{ V}$, $I_{SD} = 15\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$	-	18	-	ns
Reverse Recovery Charge	Q_{RR}		-	85	-	nC
Reverse Recovery Energy	E_{REC}		-	10.6	-	μJ

TYPICAL CHARACTERISTICS (CONTINUED)



Q_g , GATE CHARGE (nC)

Figure 7. Gate-to-Source Voltage vs. Total Charge

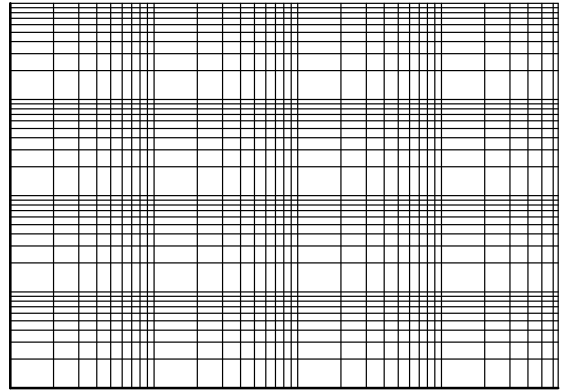
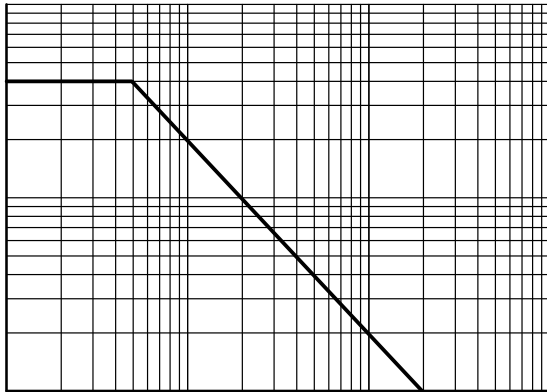


Figure 8. Capacitance vs. Drain-to-Source Voltage



t_{AV}

Figure 9. Unclamped Inductive Switching Capability

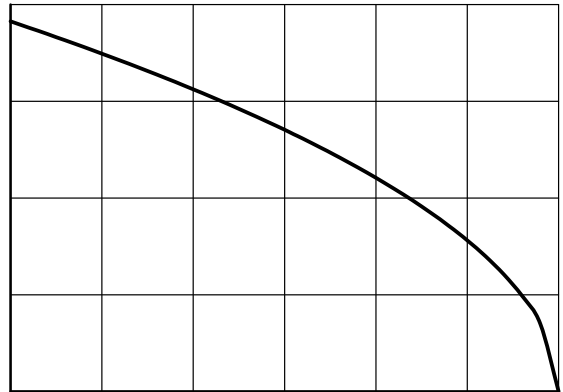
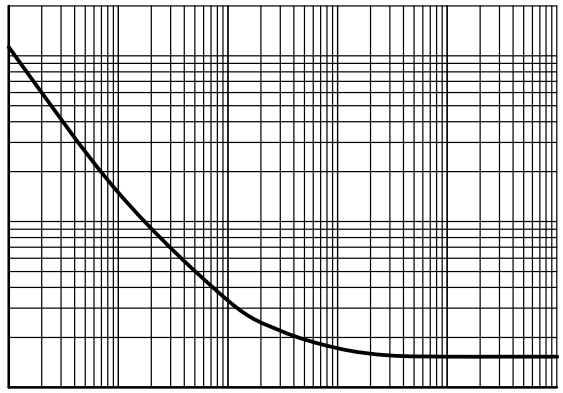
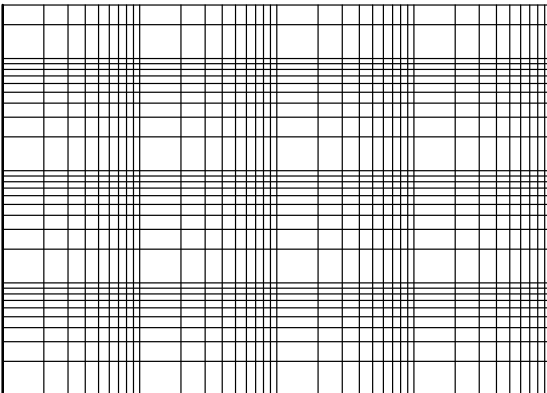


Figure 10. Maximum Continuous Drain Current vs. Case Temperature



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TYPICAL CHARACTERISTICS (CONTINUED)

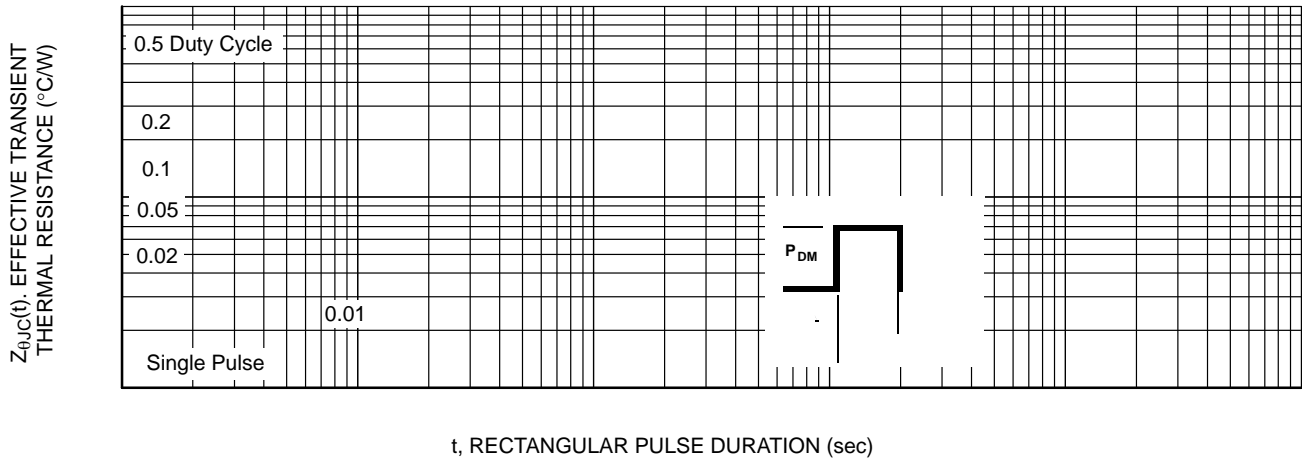


Figure 13. Junction-to-Case Thermal Response

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